

CUSTOMER

NO. MMST-A64

SUBJECT

SOT-23 TRANSISTOR, PNP, SILICON

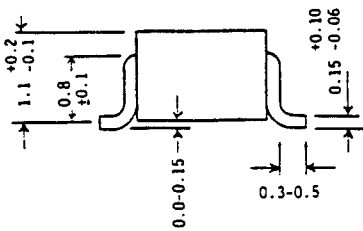
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DATE January 14, 1987

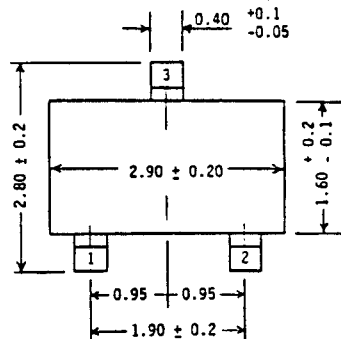
ABSOLUTE MAXIMUM RATINGS: (Ta = 25°C)

Collector-Base Voltage	V <sub>CB0</sub>	30 V
Collector-Emitter Voltage	V <sub>CE0</sub>	30 V
Emitter-Base Voltage	V <sub>EB0</sub>	10 V
Collector Current	I <sub>C</sub>	500 mA
Power Dissipation-Free Air	P <sub>D</sub>	200 mW
Power Dissipation-Ceramic Substrate	P <sub>D</sub>	350 mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150 °C
Solder Temperature (10 seconds)		260 °C

DIMENSIONS: Units (mm)



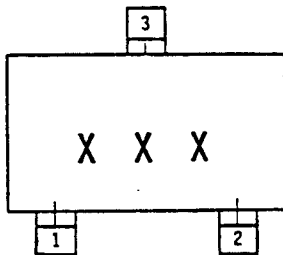
END VIEW



Pin-Out	
1	B
2	E
3	C

THE JAPANESE STYLE SC-59 PACKAGE

MARKING:



Three Digit  
Marking Code

R 2 V

PACKAGING:

- \_\_\_ BULK, 500 per BAG
- \_\_\_ MAGAZINES OF 50 EACH
- \_\_\_ 8mm T&R, T-146 3K/REEL
- \_\_\_ 8mm T&R, T-147 3K/REEL
- \_\_\_ 8mm T&R, T-24610K/REEL
- \_\_\_ 8mm T&R, T-24710K/REEL

REMARKS: PROCESS: B-25 Thermal Resistance R<sub>θJA</sub> 625 °C/Watt  
FREE AIR, T<sub>A</sub> = 25°C

**ROHM ELECTRONICS**  
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APPROVAL

CHECK

DESIGN

*[Signature]*  
10/12/87

**MASTER**

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ELECTRICAL CHARACTERISTICS: (Ta = 25°C Unless Otherwise Specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BVCES	IC = 100 uA	30			V
ICBO	VCB = 30 V		1.0	100	nA
IEBO	VEB = 10 V		1.0	100	nA
hFE	IC = 10 mA, VCE = 5 V	10,000			
hFE	IC = 100 mA, VCE = 5 V	20,000			
VCE(SAT)	IC = 100 mA, IB = 100 uA			1.5	V
VBE(ON)	IC = 100 mA, VCE = 5 V			2.0	V
fT	IC = 100 mA, VCE = 5 V, f = 100MHz	125			MHz
Cob	VCB = 10 V, IE = 0, f = 100KHz		4.0		pF
hfe	IC = 10 mA, VCE = 5 V, f = 1.0KHz		35,000		
NF	IC = 1.0 mA, VCE = 5 V, Rs = 100KΩ f = 1.0 KHz		2.0		dB

R-Ohm Corporation P.O. Box 19515 Irvine, California 92713	APPROVAL	CHECK	DESIGN
	<i>[Signature]</i> 10/12/87	✓	

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